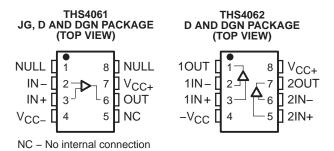
- High Speed
  - 180 MHz Bandwidth (G = 1, -3 dB)
  - 400 V/µs Slew Rate
  - 40-ns Settling Time (0.1%)
- High Output Drive, I<sub>O</sub> = 115 mA (typ)
- Excellent Video Performance
  - 75 MHz 0.1 dB Bandwidth (G = 1)
  - 0.02% Differential Gain
  - 0.02° Differential Phase
- Very Low Distortion
  - THD = -72 dBc at f = 1 MHz
- Wide Range of Power Supplies
  - $V_{CC}$  =  $\pm 5$  V to  $\pm 15$  V
- Available in Standard SOIC, MSOP PowerPAD™, JG, or FK Package
- Evaluation Module Available

#### description

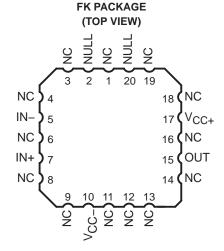
The THS4061 and THS4062 are generalpurpose, single/dual, high-speed voltage feedback amplifiers ideal for a wide range of applications including video, communication, and imaging. The devices offer very good ac performance with 180-MHz bandwidth, 400-V/µs slew rate, and 40-ns settling time (0.1%). The THS4061/2 are stable at all gains for both inverting and noninverting configurations. These amplifiers have a high output drive capability of 115 mA and draw only 7.8 mA supply current per channel. Excellent professional video results can be obtained with the low differential gain/phase errors of 0.02%/0.02° and wide 0.1 db flatness to 75 MHz. For applications requiring low distortion, the THS4061/2 is ideally suited with total harmonic distortion of -72 dBc at f = 1 MHz.

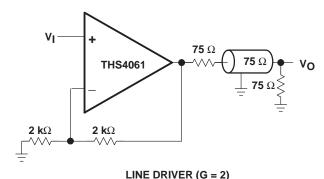




Cross-Section View Showing PowerPAD Option (DGN)

THS4061







CAUTION: The THS4061 and THS4062 provide ESD protection circuitry. However, permanent damage can still occur if this device is subjected to high-energy electrostatic discharges. Proper ESD precautions are recommended to avoid any performance degradation or loss of functionality



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments Incorporated.



	RELATED DEVICES
DEVICE	DESCRIPTION
THS4011/2	290-MHz Low Distortion High-Speed Amplifiers
THS4031/2	100-MHz Low Noise High Speed-Amplifiers
THS4061/2	180-MHz High-Speed Amplifiers

#### **AVAILABLE OPTIONS**

			PACKAGED DEVICES				
TA	NUMBER OF CHANNELS	PLASTIC SMALL OUTLINE <sup>†</sup> (D)	PLASTIC MSOP† (DGN)	CERAMIC DIP (JG)	CHIP CARRIER (FK)	MSOP SYMBOL	EVALUATION MODULES
0°C to	1	THS4061CD	THS4061CDGN	_	_	TIABS	THS4061EVM
70°C	2	THS4062CD	THS4062CDGN	_	_	TIABM	THS4062EVM
−40°C to	1	THS4061ID	THS4061IDGN	_	_	TIABT	_
85°C	2	THS4062ID	THS4062IDGN	_	_	TIABN	_
–55°C to 125°C	1	_	_	THS4061MJG	THS4061MFK	_	_

<sup>†</sup> The D and DGN packages are available taped and reeled. Add an R suffix to the device type (i.e., THS4061CDGNR).

#### functional block diagram

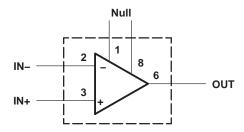


Figure 1. THS4061 - Single Channel

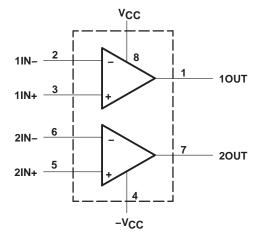


Figure 2. THS4062 - Dual Channel



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#### absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, V <sub>CC</sub> + to V <sub>CC</sub>		33 V
Output current, IO		150 mÅ
Differential input voltage, V <sub>IO</sub>		±4 V
Continuous total power dissipation		. See Dissipation Rating Table
Maximum junction temperature, T <sub>J</sub>		150°C
Operating free-air temperature, T <sub>A</sub> :	C-suffix	
	I-suffix	–40°C to 85°C
	M-suffix	–55°C to 125°C
Storage temperature, T <sub>stq</sub>		–65°C to 150°C
	ch) from case for 10 seconds, D and DGN	
Lead temperature 1,6 mm (1/16 inc	ch) from case for 60 seconds, JG package	300°C
Case temperature for 60 seconds,	FK package	260°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **DISSIPATION RATING TABLE**

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D	740 mW	6 mW/°C	475 mW	385 mW	_
DGN <sup>‡</sup>	2.14 W	17.1 mW/°C	1.37 W	1.11 W	<u> </u>
JG	1057 mW	8.4 mW/°C	627 mW	546 mW	210 mW
FK	1375 mW	11 mW/°C	880 mW	715 mW	275 mW

<sup>&</sup>lt;sup>‡</sup> The DGN package incorporates a PowerPAD on the underside of the device. This acts as a heatsink and must be connected to a thermal dissipation plane for proper power dissipation. Failure to do so can result in exceeding the maximum specified junction temperature, which could permanently damage the device.

#### recommended operating conditions

		MIN	NOM MAX	UNIT
Own book to be War and War	Dual supply	±4.5	±16	.,
Supply voltage, V <sub>CC</sub> + and V <sub>CC</sub> -	Single supply	9	32	V
	C-suffix	0	70	
Operating free-air temperature, TA	I-suffix	-40	85	°C
	M-suffix	-55	125	



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## electrical characteristics at T<sub>A</sub> = 25°C, V<sub>CC</sub> = $\pm 15$ V, R<sub>L</sub> = 150 $\Omega$ (unless otherwise noted)

#### dynamic performance

	PARAMETER	TEST CONDITIONS†		THS4061C/I, THS4062C/I			UNIT	
				MIN .	TYP	MAX		
	Dynamic performance small-signal bandwidth (–3 dB)	$V_{CC} = \pm 5 \text{ V}$	Gain = 1		180		MHz	
		V <sub>CC</sub> = ±15 V	Coin 4		50		MHz	
BW	bandwidth ( 5 db)	V <sub>CC</sub> = ±5 V	Gain = -1		50		IVIHZ	
	Bandwidth for 0.1 dB flatness	V <sub>CC</sub> = ±15 V	Coin 4	75			MHz	
		V <sub>CC</sub> = ±5 V	Gain = 1		20		IVIMZ	
CD	Classification	$V_{CC} = \pm 15 \text{ V}$	Coin 4		400			
SR	Slew rate	$V_{CC} = \pm 5 \text{ V}$	Gain = -1		350		V/μs	
	Cattlian times to 0.400	$V_{CC} = \pm 15 \text{ V},  5-\text{V step } (0 \text{ V to } 5 \text{ V})$	Onin 4		40		ns	
	Settling time to 0.1%	$V_{CC} = \pm 5 \text{ V}, \qquad V_{O} = -2.5 \text{ V to } 2.5 \text{ V},$	Gain = -1		40			
t <sub>S</sub>	Sottling time to 0.049/	$V_{CC} = \pm 15 \text{ V},  5-\text{V step } (0 \text{ V to } 5 \text{ V})$	Coin 1		140		ns	
	Settling time to 0.01%	$V_{CC} = \pm 5 \text{ V}, \qquad V_{O} = -2.5 \text{ V to } 2.5 \text{ V},$	Gain = −1		150			

<sup>†</sup> Full range = 0°C to 70°C for C suffix and -40°C to 85°C for I suffix

#### noise/distortion performance

	PARAMETER	TEST CONDITIONS <sup>†</sup>			THS4061C/I, THS4062C/I			UNIT
							MAX	
THD	Total harmonic distortion	f = 1 MHz				-72		dBc
V <sub>n</sub>	Input voltage noise	f = 10 kHz,	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$			14.5		nV/√ <del>Hz</del>
In	Input current noise	f = 10 kHz,	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	_		1.6		pA/√ <del>Hz</del>
	D		NTOO 10 IDE 11 ii	V <sub>CC</sub> = ±15 V		0.02 %		
	Differential gain error	Gain = 2,	NTSC, 40 IRE modulation	V <sub>CC</sub> = ±5 V		0.02 %		
	D''' .: 1 . 1		NITOO 40 IDE 11 6	V <sub>CC</sub> = ±15 V		0.02°		
	Differential phase error	Gain = 2,	NTSC, 40 IRE modulation	$V_{CC} = \pm 5 \text{ V}$		0.06°		
	Channel-to-channel crosstalk (THS4062 only)	V <sub>CC</sub> = ±5 V (	or ±15 V, f = 1 MHz			65		dB

<sup>†</sup> Full range = 0°C to 70°C for C suffix and -40°C to 85°C for I suffix

#### dc performance

PARAMETER		TEST CONDITIONS†	TEST CONDITIONS <sup>†</sup>			THS4061C/I, THS4062C/I		
				MIN	TYP	MAX		
		V 45V V 40V B 410	T <sub>A</sub> = 25°C	5	15		\//\/	
	Open loop gain	$V_{CC} = \pm 15 \text{ V},  V_{O} = \pm 10 \text{ V},  R_{L} = 1 \text{ k}\Omega$	T <sub>A</sub> = full range	4			V/mV	
Open loop gain		V 15V V 105V D 110	T <sub>A</sub> = 25°C	2.5	8		\//\/	
		$V_{CC} = \pm 5 \text{ V}, \qquad V_{O} = \pm 2.5 \text{ V},  R_{L} = 1 \text{ k}\Omega$	T <sub>A</sub> = full range	2			V/mV	
.,	Input offset voltage	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	_ , , ,		2.5	8	mV	
Vos	Offset drift	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	T <sub>A</sub> = full range		15	MAX	μV/°C	
I <sub>IB</sub>	Input bias current	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	T <sub>A</sub> = full range		3	6	μΑ	
los	Input offset current	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	T <sub>A</sub> = full range		75	250	nA	
	Offset current drift	T <sub>A</sub> = full range			0.3		nA/°C	

<sup>†</sup> Full range = 0°C to 70°C for C suffix and -40°C to 85°C for I suffix



# electrical characteristics at $T_A$ = 25°C, $V_{CC}$ = $\pm 15$ V, $R_L$ = 150 $\Omega$ (unless otherwise noted) (continued) input characteristics

	PARAMETER		TEST CONDITIONS <sup>†</sup>			THS4061C/I, THS4062C/I		
					MIN	TYP	MAX	
V Common weeks installed the second		$V_{CC} = \pm 15 \text{ V}$			±13.8	±14.1		.,
VICR	Common-mode input voltage range	V <sub>CC</sub> = ±5 V			±3.8	±4.3		٧
CMDD	Common mode minution matic	$V_{CC} = \pm 15 \text{ V},$	$V_{ICR} = \pm 12 V$	T <sub>A</sub> = full range	70	110		dB
CMRR	Common mode rejection ratio	$V_{CC} = \pm 5 \text{ V},$	V <sub>ICR</sub> = ±2.5 V		70	95		
R <sub>I</sub>	Input resistance		•			1		МΩ
Ci	Input capacitance					2		pF

<sup>†</sup> Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

#### output characteristics

	PARAMETER	TEST CO	TEST CONDITIONS†			THS4061C/I, THS4062C/I		
					TYP	MAX		
V		V <sub>CC</sub> = ±15 V	$R_L = 250 \Omega$	±11.5	±12.5			
	0	V <sub>CC</sub> = ±5 V	$R_L = 150 \Omega$	±3.2	±3.5		V	
VO	Output voltage swing	V <sub>CC</sub> = ±15 V	5 410	±13	±13.5		.,	
		V <sub>CC</sub> = ±5 V	$R_L = 1 \text{ k}\Omega$	±3.5	±3.7		V	
	Output summed	V <sub>CC</sub> = ±15 V	D 000	80	115		4	
Ю	Output current	$R_L = 20 \Omega$	50	75		mA		
Isc	Short-circuit current	V <sub>CC</sub> = ±15 V			150		mA	
RO	Output resistance	Open loop			12		Ω	

<sup>†</sup> Full range = 0°C to 70°C for C suffix and -40°C to 85°C for I suffix

#### power supply

PARAMETER		TEST CONDITIONS	TEST CONDITIONS†			THS4061C/I, THS4062C/I			
				MIN	TYP	MAX			
V Constant to the second for the second		Dual supply	Dual supply			±16.5			
VCC	Supply voltage operating range	Single supply				33	V		
		V <sub>CC</sub> = ±15 V			7.8	10.5			
ICC	Quiescent current (per amplifier)	V <sub>CC</sub> = ±5 V	T <sub>A</sub> = full range		7.3	10	mA		
			T <sub>A</sub> = 25°C	70	78				
PSRR	Power supply rejection ratio	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	T <sub>A</sub> = full range	68			dB		

<sup>†</sup> Full range = 0°C to 70°C for C suffix and -40°C to 85°C for I suffix



#### THS4061, THS4062 180-MHz HIGH-SPEED AMPLIFIERS

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### electrical characteristics at T<sub>A</sub> = 25°C, V<sub>CC</sub> = $\pm$ 15 V, R<sub>L</sub> = 150 $\Omega$ (unless otherwise noted)

#### dynamic performance

	24244555		TEST SOMBITIONS!		THS4061M				
	PARAMETER		TEST CONDITIONS†			TYP	MAX	UNIT	
	Unity-gain bandwidth	Closed loop,	$R_L = 1 \text{ k}\Omega$	$V_{CC} = \pm 15 \text{ V}$	*140	180		MHz	
BW		$V_{CC} = \pm 15 \text{ V}$		Caia 4		180		N.41.1-	
	Dynamic performance small-signal	V <sub>CC</sub> = ±5 V		Gain = 1		180		MHz	
	bandwidth (-3 dB)	$V_{CC} = \pm 15 \text{ V}$			50				
		$V_{CC} = \pm 5 \text{ V}$		Gain = -1		50		MHz	
		$V_{CC} = \pm 15 \text{ V}$				75		MHz	
	Bandwidth for 0.1 dB flatness	V <sub>CC</sub> = ±5 V		Gain = 1		20			
SR	Slew rate	$V_{CC} = \pm 15 \text{ V}$	$R_L = 1 k\Omega$		*400	500		V/μs	
	Califforn Cara to 0.40/	$V_{CC} = \pm 15 \text{ V},$	5-V step (0 V to 5 V)	0-1-		40		ns	
t <sub>S</sub>	Settling time to 0.1%	$V_{CC} = \pm 5 \text{ V},$	$V_0 = -2.5 \text{ V to } 2.5 \text{ V},$	Gain = -1		40			
	Settling time to 0.01%	$V_{CC} = \pm 15 \text{ V},$	5-V step (0 V to 5 V)	Coin 1		140		ns	
		$V_{CC} = \pm 5 \text{ V},$	$V_0 = -2.5 \text{ V to } 2.5 \text{ V},$	Gain = -1		150			

<sup>†</sup> Full range =  $-55^{\circ}$ C to 125°C for M suffix

#### noise/distortion performance

			TEST SOURITIONS!		THS4061M			
	PARAMETER		TEST CONDITIONS†		MIN	TYP	MAX	UNIT
THD	Total harmonic distortion	f = 1 MHz				-72		dBc
٧n	Input voltage noise	f = 10 kHz,	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$			14.5		nV/√ <del>Hz</del>
In	Input current noise	f = 10 kHz,	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$			1.6		pA/√ <del>Hz</del>
	Differential main arms	Onia O	NTOO 40 IDE Madelation	$V_{CC} = \pm 15 \text{ V}$		0.02		0/
	Differential gain error	Gain = 2,	NTSC, 40 IRE Modulation	$V_{CC} = \pm 5 \text{ V}$		0.02		%
	Differential phase arror	Coin 2	NTCC 40 IDE Modulation	$V_{CC} = \pm 15 \text{ V}$		0.02°		
	Differential phase error	Gain = 2, NTSC, 40 IRE Modulation		V <sub>CC</sub> = ±5 V		0.06°		

<sup>†</sup> Full range = -55°C to 125°C for M suffix

#### dc performance

	DADAMETED	TEOT	CONDITIONS		TH	1S4061N	Л	UNIT
	PARAMETER	IESI	CONDITIONS		MIN	TYP	MAX	UNII
	On an Inna mala	$V_{CC} = \pm 15 \text{ V},  V_{O} = \pm 10$	V, $R_L = 1 k\Omega$	T 6.00	5	9		
Open loop gain		$V_{CC} = \pm 5 \text{ V}, \qquad V_{O} = \pm 2.5 \text{ V}$	T <sub>A</sub> = full range	2.5	6		V/mV	
	Input offset voltage	V 15 V on 145 V	D 4160	T <sub>A</sub> = 25°C		2.5	8	mV
۷ <sub>IO</sub>		$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	$R_L = 1 k\Omega$	T <sub>A</sub> = full range			9	mV
	Offset drift	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	$R_L = 1 \text{ k}\Omega$	T <sub>A</sub> = full range		15		μV/°C
I <sub>IB</sub>	Input bias current	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	$R_L = 1 \text{ k}\Omega$	T <sub>A</sub> = full range		3	6	μΑ
ΙΙΟ	Input offset current	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	$R_L = 1 \text{ k}\Omega$	T <sub>A</sub> = full range		75	250	nA
	Offset current drift	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	$R_L = 1 \text{ k}\Omega$	T <sub>A</sub> = full range		0.3		nA/°C

<sup>†</sup> Full range =  $-55^{\circ}$ C to 125°C for M suffix



<sup>\*</sup>This parameter is not tested.

# electrical characteristics at $T_A$ = full range, $V_{CC}$ = $\pm 15$ V, $R_L$ = 1 k $\Omega$ (unless otherwise noted) (continued)

#### input characteristics

	24244555	TEGT CONDITIONS!	T			
	PARAMETER	TEST CONDITIONS†	MIN	TYP	MAX	UNIT
.,	Opening the least control to the control of	$V_{CC} = \pm 15 \text{ V}$	±13.8	±14.1		
VICR	Common-mode input voltage range	V <sub>CC</sub> = ±5 V	±3.8	±4.3		V
CMDD	Common mode minetics matic	$V_{CC} = \pm 15 \text{ V}, \qquad V_{ICR} = \pm 12 \text{ V}$	70	86		40
CMRR	Common mode rejection ratio	$V_{CC} = \pm 5 \text{ V}, \qquad V_{ICR} = \pm 2.5 \text{ V}$	80	90		dB
R <sub>I</sub>	Input resistance			1		MΩ
Ci	Input capacitance			2		pF

<sup>†</sup> Full range = -55°C to 125°C for M suffix

#### output characteristics

	242445772			Т	Л		
	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
		V <sub>CC</sub> = ±15 V	$R_L = 250 \Omega$	±12	±13.1		
V <sub>O</sub> Output	Output walks are suited	V <sub>CC</sub> = ±5 V	$R_L = 150 \Omega$	±3.2	±3.5		V
	Output voltage swing	V <sub>CC</sub> = ±15 V	D 410	±13	±13.5		V
		V <sub>CC</sub> = ±5 V	$R_L = 1 k\Omega$	±3.5	±3.7		
	• • •	V <sub>CC</sub> = ±15 V	<b>D 20</b> 0	70	115		
Ю	Output current	V <sub>CC</sub> = ±5 V	$R_L = 20 \Omega$	50	75		mA
ISC	Short-circuit current	V <sub>CC</sub> = ±15 V	T <sub>A</sub> = 25°C		150		mA
RO	Output resistance	Open loop			12	·	Ω

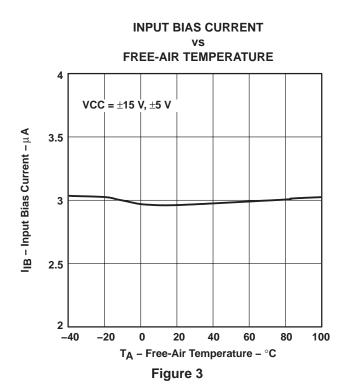
<sup>†</sup> Full range = -55°C to 125°C for M suffix

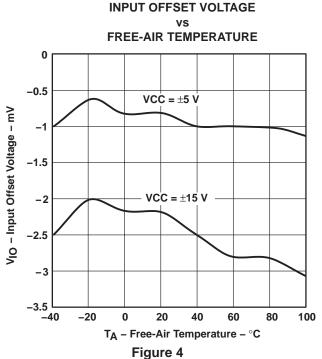
#### power supply

				TH	1S4061	VI	
	PARAMETER	TEST CONDITIO	NSI	MIN	TYP	MAX	UNIT
V	Complex colleges on creating an area	Dual supply		±4.5		±16.5	, l
VCC	Supply voltage operating range	Single supply		9		33	V
	Ī	V <sub>CC</sub> = ±15 V	T. 050C		7.8	9	
١.		V <sub>CC</sub> = ±5 V	T <sub>A</sub> = 25°C		7.3	8.5	
Icc	Quiescent current	V <sub>CC</sub> = ±15 V	T 6.11			11	mA
		$V_{CC} = \pm 5 \text{ V}$	T <sub>A</sub> = full range			10.5	
DCDD	Power aupply rejection ratio	Vo a - +5 V or +15 V	T <sub>A</sub> = 25°C	76	80		dB
PSRR	Power supply rejection ratio	$V_{CC} = \pm 5 \text{ V or } \pm 15 \text{ V}$	T <sub>A</sub> = full range	74	78		uБ

<sup>†</sup> Full range =  $-55^{\circ}$ C to 125°C for M suffix

			FIGURE
I <sub>IB</sub>	Input bias current	vs Free-air temperature	3
VIO	Input offset voltage	vs Free-air temperature	4
	Open-loop gain	vs Frequency	5
	Phase	vs Frequency	5
	Differential gain	vs Number of loads	6, 8
	Differential phase	vs Number of loads	7, 9
	Closed-loop gain	vs Frequency	10, 11
	Output amplitude	vs Frequency	12, 13
CMRR	Common-mode rejection ratio	vs Frequency	14
		vs Frequency	15
PSRR	Power supply rejection ratio	vs Free-air temperature	16
VO(PP)	Output voltage swing	vs Supply voltage	17
ICC	Supply current	vs Free-air temperature	18
Env	Noise spectral density	vs Frequency	19
THD	Total harmonic distortion	vs Frequency	20, 21
	Crosstalk	vs Frequency	22, 23



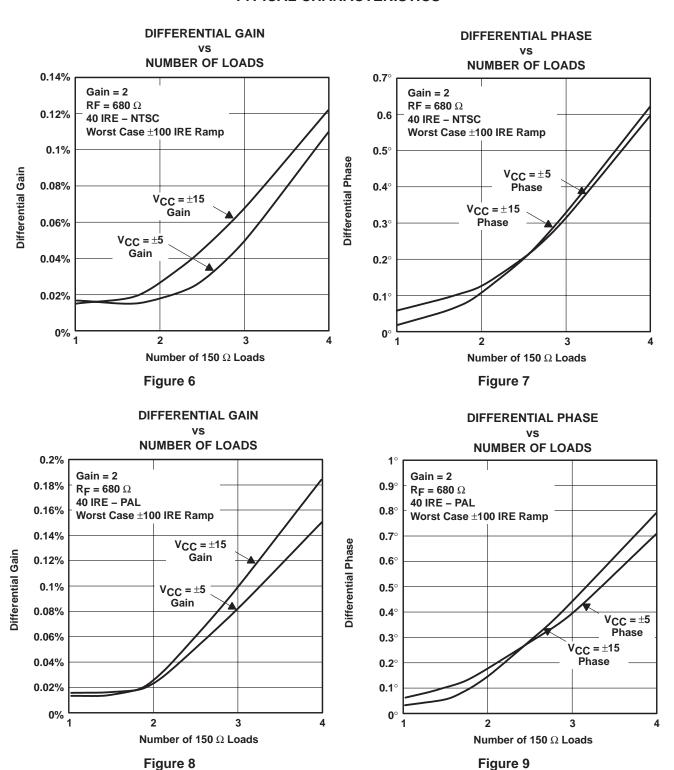


#### **OPEN-LOOP GAIN AND PHASE**

#### vs **FREQUENCY** 90 80 **0**° 70 Open-Loop Gain - dB 60 –45° Phase 50 40 **-90**° 30 20 -135° 10 0 –180° 10M 1k 10k 100k 1M 100M 1G f - Frequency - Hz



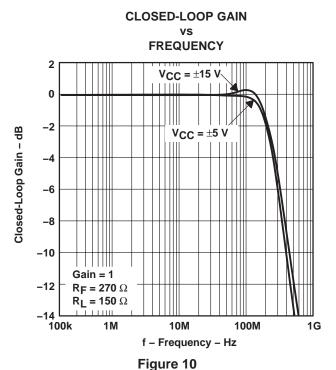
Figure 5

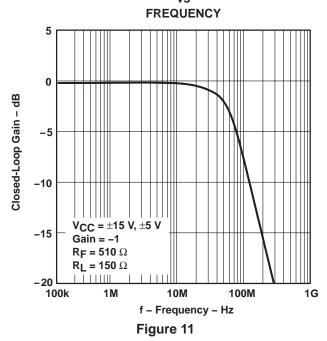




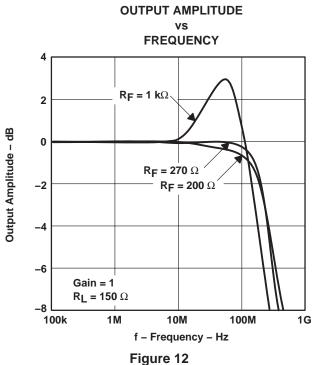
**CLOSED-LOOP GAIN** 

#### **TYPICAL CHARACTERISTICS**





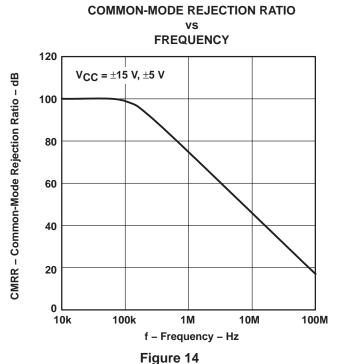
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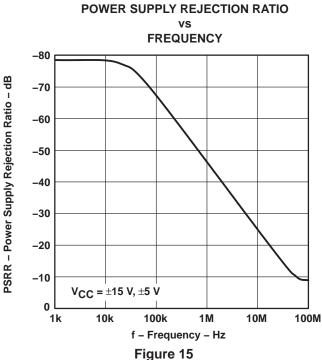


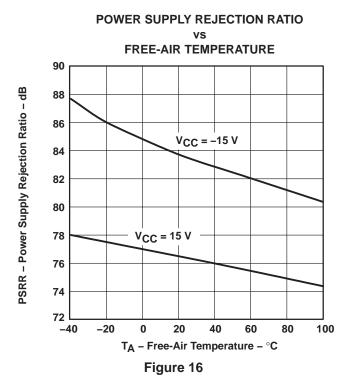
**OUTPUT AMPLITUDE FREQUENCY** 2  $R_F = 510 \Omega$ 0 Output Amplitude - dB  $R_F = 3 k\Omega$ -2 -4 -6 -8 Gain = -1 $R_L = 150 \Omega$ -10 100k 1M 10M 100M 1**G** f - Frequency - Hz

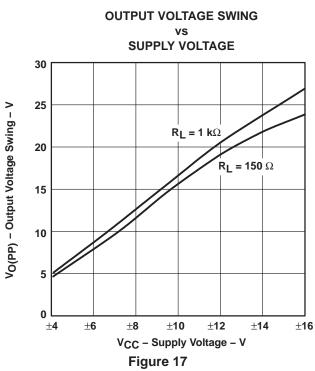
Figure 13

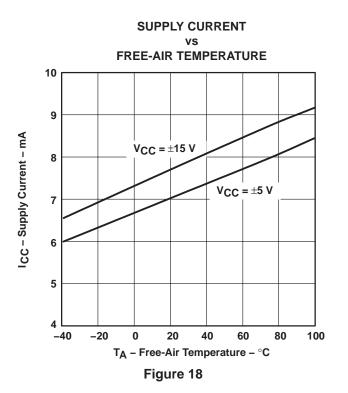
TEXAS INSTRUMENTS
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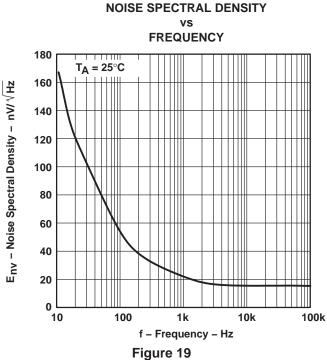


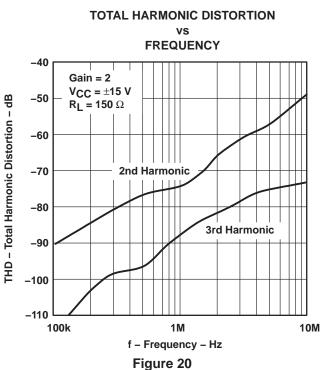


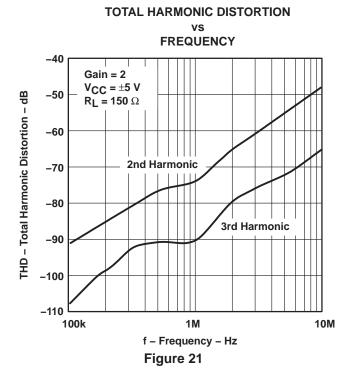


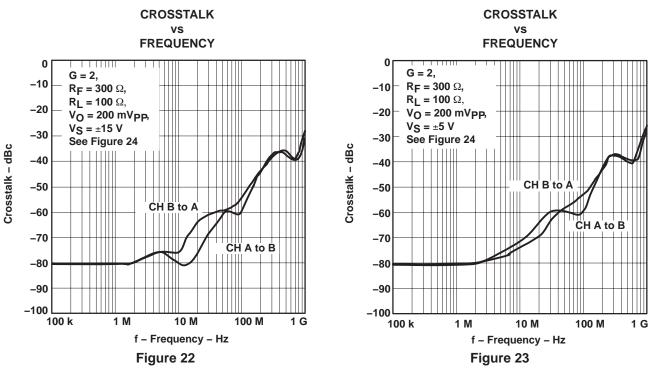












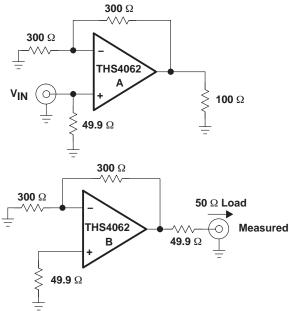


Figure 24. Test Circuits

#### theory of operation

The THS406x is a high speed, operational amplifier configured in a voltage feedback architecture. It is built using a 30-V, dielectrically isolated, complementary bipolar process with NPN and PNP transistors possessing  $f_{TS}$  of several GHz. This results in an exceptionally high performance amplifier that has a wide bandwidth, high slew rate, fast settling time, and low distortion. A simplified schematic is shown in Figure 25.

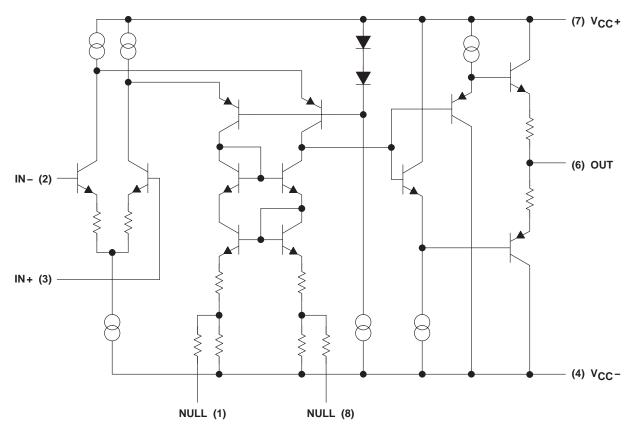


Figure 25. THS4061 Simplified Schematic

#### offset nulling

The THS4061 has very low input offset voltage for a high-speed amplifier. However, if additional correction is required, an offset nulling function has been provided. By placing a potentiometer between terminals 1 and 8 and tying the wiper to the negative supply, the input offset can be adjusted. This is shown in Figure 26.

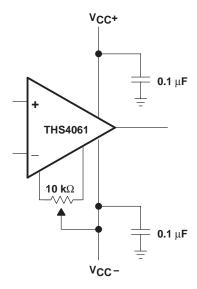


Figure 26. Offset Nulling Schematic

#### optimizing unity gain response

Internal frequency compensation of the THS406x was selected to provide very wideband performance yet still maintain stability when operated in a noninverting unity gain configuration. When amplifiers are compensated in this manner there is usually peaking in the closed loop response and some ringing in the step response for very fast input edges, depending upon the application. This is because a minimum phase margin is maintained for the G=+1 configuration. For optimum settling time and minimum ringing, a feedback resistor of 270  $\Omega$  should be used as shown in Figure 27. Additional capacitance can also be used in parallel with the feedback resistance if even finer optimization is required.

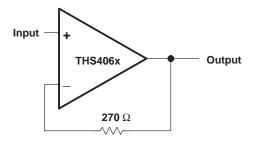


Figure 27. Noninverting, Unity Gain Schematic



#### driving a capacitive load

Driving capacitive loads with high performance amplifiers is not a problem as long as certain precautions are taken. The first is to realize that the THS406x has been internally compensated to maximize its bandwidth and slew rate performance. When the amplifier is compensated in this manner, capacitive loading directly on the output will decrease the device's phase margin leading to high frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, it is recommended that a resistor be placed in series with the output of the amplifier, as shown in Figure 28. A minimum value of 20  $\Omega$  should work well for most applications. For example, in 75- $\Omega$  transmission systems, setting the series resistor value to 75  $\Omega$  both isolates any capacitance loading and provides the proper line impedance matching at the source end.

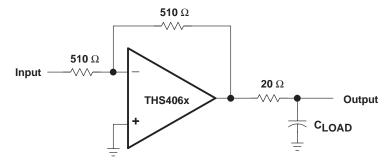


Figure 28. Driving a Capacitive Load

#### circuit layout considerations

In order to achieve the levels of high frequency performance of the THS406x, it is essential that proper printed-circuit board high frequency design techniques be followed. A general set of guidelines is given below. In addition, a THS406x evaluation board is available to use as a guide for layout or for evaluating the device performance.

- Ground planes It is highly recommended that a ground plane be used on the board to provide all
  components with a low inductive ground connection. However, in the areas of the amplifier inputs and
  output, the ground plane can be removed to minimize the stray capacitance.
- Proper power supply decoupling Use a 6.8-μF tantalum capacitor in parallel with a 0.1-μF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-μF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-μF capacitor should be placed as close as possible to the supply terminal. As this distances increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- Sockets Sockets are not recommended for high-speed operational amplifiers. The additional lead inductance in the socket pins will often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board is the best implementation.
- Short trace runs/compact part placements Optimum high frequency performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This helps to minimize stray capacitance at the input of the amplifier.



#### circuit layout considerations (continued)

 Surface-mount passive components – Using surface-mount passive components is recommended for high-frequency amplifier circuits for several reasons. First, because of the extremely low lead inductance of surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small size of surface-mount components naturally leads to a more compact layout, thereby minimizing both stray inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be kept as short as possible.

#### evaluation board

An evaluation board is available for the THS4061 (literature number SLOP226) and THS4062 (literaure number SLOP235). This board has been configured for very low parasitic capacitance in order to realize the full performance of the amplifier. A schematic of the evaluation board is shown in Figure 29. The circuitry has been designed so that the amplifier may be used in either an inverting or noninverting configuration. To order the evaluation board contact your local TI sales office or distributor. For more detailed information, refer to the THS4061 EVM User's Manual (literature number SLOU038) or the THS4062 EVM User's Manual (literature number SLOU040)

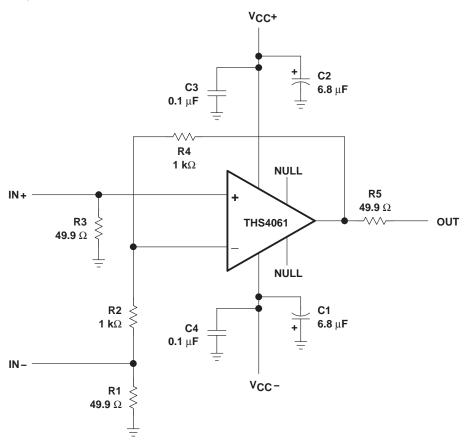


Figure 29. THS4061 Evaluation Board Schematic





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#### **PACKAGING INFORMATION**

S982-998010102A	Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp (3)
THS4061CD	5962-9960101Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
No. Sb/Br	5962-9960101QPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
Name	THS4061CD	ACTIVE	SOIC	D	8	75	,	CU NIPDAU	Level-1-260C-UNLIM
Power PAD	THS4061CDG4	ACTIVE	SOIC	D	8	75	,	CU NIPDAU	Level-1-260C-UNLIM
Power PAD	THS4061CDGN	ACTIVE	Power	DGN	8	80		CU NIPDAU	Level-1-260C-UNLIM
Power PAD	THS4061CDGNG4	ACTIVE	Power	DGN	8	80	•	CU NIPDAU	Level-1-260C-UNLIM
Power PAD	THS4061CDGNR	ACTIVE	Power	DGN	8	2500	•	CU NIPDAU	Level-1-260C-UNLIM
THS4061CDRG4	THS4061CDGNRG4	ACTIVE	Power	DGN	8	2500	•	CU NIPDAU	Level-1-260C-UNLIM
THS4061ID	THS4061CDR	ACTIVE	SOIC	D	8	2500		CU NIPDAU	Level-1-260C-UNLIM
THS4061IDG4	THS4061CDRG4	ACTIVE	SOIC	D	8	2500	•	CU NIPDAU	Level-1-260C-UNLIM
THS4061IDGNR	THS4061ID	ACTIVE	SOIC	D	8	75	•	CU NIPDAU	Level-1-260C-UNLIM
Power PAD	THS4061IDG4	ACTIVE	SOIC	D	8	75	,	CU NIPDAU	Level-1-260C-UNLIM
Power PAD	THS4061IDGNR	ACTIVE	Power	DGN	8	2500		CU NIPDAU	Level-1-260C-UNLIM
THS4061IDRG4	THS4061IDGNRG4	ACTIVE	Power	DGN	8	2500	•	CU NIPDAU	Level-1-260C-UNLIM
THS4061MFKB	THS4061IDR	ACTIVE	SOIC	D	8	2500	•	CU NIPDAU	Level-1-260C-UNLIM
THS4061MJG         ACTIVE         CDIP         JG         8         1         TBD         A42         N / A for Pkg Type           THS4061MJGB         ACTIVE         CDIP         JG         8         1         TBD         A42         N / A for Pkg Type           THS4062CD         ACTIVE         SOIC         D         8         75         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDG4         ACTIVE         SOIC         D         8         75         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDGN         ACTIVE         MSOP- Power PAD         B         8         80         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDGNG4         ACTIVE         MSOP- DGN         8         80         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)	THS4061IDRG4	ACTIVE	SOIC	D	8	2500	`	CU NIPDAU	Level-1-260C-UNLIM
THS4061MJGB         ACTIVE         CDIP         JG         8         1         TBD         A42         N / A for Pkg Type           THS4062CD         ACTIVE         SOIC         D         8         75         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDG4         ACTIVE         SOIC         D         8         75         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDGN         ACTIVE         MSOP-Power PAD         B         8         80         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDGNG4         ACTIVE         MSOP-Power PAD         B         8         80         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)	THS4061MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
THS4062CD         ACTIVE         SOIC         D         8         75         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDG4         ACTIVE         SOIC         D         8         75         Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)           THS4062CDGN         ACTIVE         MSOP- DGN	THS4061MJG	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
THS4062CDG4	THS4061MJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
THS4062CDGN ACTIVE MSOP- DGN 8 80 Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)  THS4062CDGNG4 ACTIVE MSOP- DGN 8 80 Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)  Power PAD  THS4062CDGNG4 ACTIVE MSOP- DGN 8 80 Green (RoHS & CU NIPDAU Level-1-260C-UNLIM no Sb/Br)	THS4062CD	ACTIVE	SOIC	D	8	75		CU NIPDAU	Level-1-260C-UNLIM
Power no Sb/Br) PAD  THS4062CDGNG4 ACTIVE MSOP- DGN 8 80 Green (RoHS & CU NIPDAU Level-1-260C-UNLIM Power no Sb/Br) PAD	THS4062CDG4	ACTIVE	SOIC	D	8	75		CU NIPDAU	Level-1-260C-UNLIM
Power no Sb/Br) PAD	THS4062CDGN	ACTIVE	Power	DGN	8	80	,	CU NIPDAU	Level-1-260C-UNLIM
THS4062CDR ACTIVE SOIC D 8 2500 Green (RoHS & CU NIPDAU Level-1-260C-UNLIM	THS4062CDGNG4	ACTIVE	Power	DGN	8	80	•	CU NIPDAU	Level-1-260C-UNLIM
	THS4062CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS &	CU NIPDAU	Level-1-260C-UNLIM

#### PACKAGE OPTION ADDENDUM

www.ti.com 15-Oct-2009

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
						no Sb/Br)		
THS4062CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDGN	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDGNG4	ACTIVE	MSOP- Power PAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDGNR	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDGNRG4	ACTIVE	MSOP- Power PAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
THS4062IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND**: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <a href="http://www.ti.com/productcontent">http://www.ti.com/productcontent</a> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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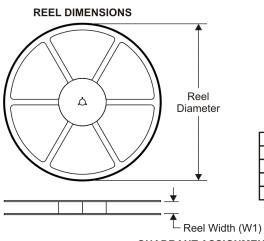


#### **PACKAGE OPTION ADDENDUM**

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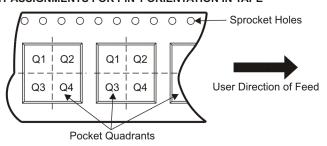
#### TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

ΛΩ	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
	Overall width of the carrier tape
P1	Pitch between successive cavity centers

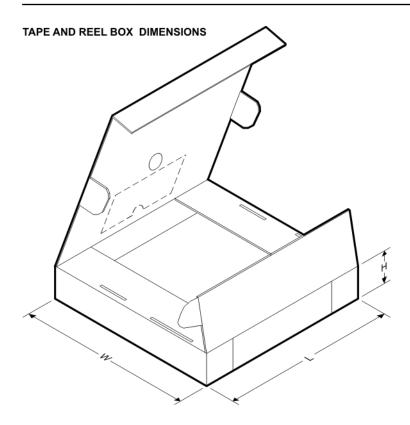
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS4061CDGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.2	3.3	1.6	8.0	12.0	Q1
THS4061CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THS4061IDGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.2	3.3	1.6	8.0	12.0	Q1
THS4061IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THS4062CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THS4062IDGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.2	3.3	1.6	8.0	12.0	Q1
THS4062IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1





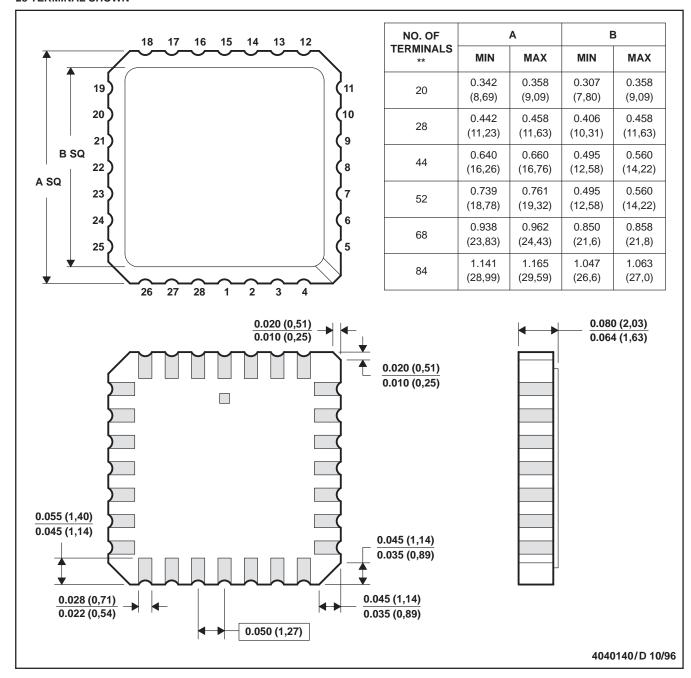
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS4061CDGNR	MSOP-PowerPAD	DGN	8	2500	338.1	340.5	21.1
THS4061CDR	SOIC	D	8	2500	346.0	346.0	29.0
THS4061IDGNR	MSOP-PowerPAD	DGN	8	2500	338.1	340.5	21.1
THS4061IDR	SOIC	D	8	2500	346.0	346.0	29.0
THS4062CDR	SOIC	D	8	2500	346.0	346.0	29.0
THS4062IDGNR	MSOP-PowerPAD	DGN	8	2500	338.1	340.5	21.1
THS4062IDR	SOIC	D	8	2500	346.0	346.0	29.0

#### FK (S-CQCC-N\*\*)

#### **28 TERMINAL SHOWN**

#### **LEADLESS CERAMIC CHIP CARRIER**

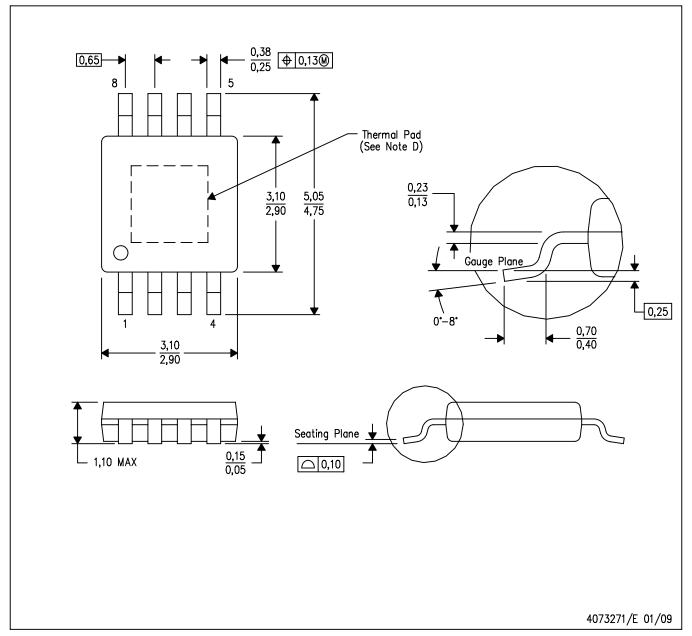


NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. The terminals are gold plated.
- E. Falls within JEDEC MS-004



DGN (S-PDSO-G8) PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="http://www.ti.com">www.ti.com</a> <a href="http://www.ti.com">http://www.ti.com</a>.
- E. Falls within JEDEC MO-187 variation AA-T

PowerPAD is a trademark of Texas instruments.



#### THERMAL PAD MECHANICAL DATA



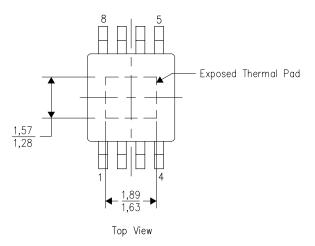
DGN (S-PDSO-G8)

#### THERMAL INFORMATION

This PowerPAD  $^{\text{M}}$  package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

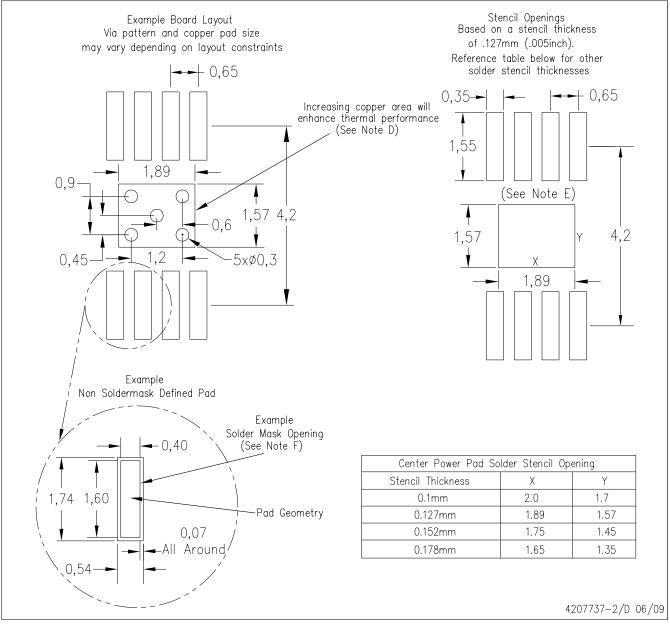
The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

## DGN (R-PDSO-G8) PowerPAD™



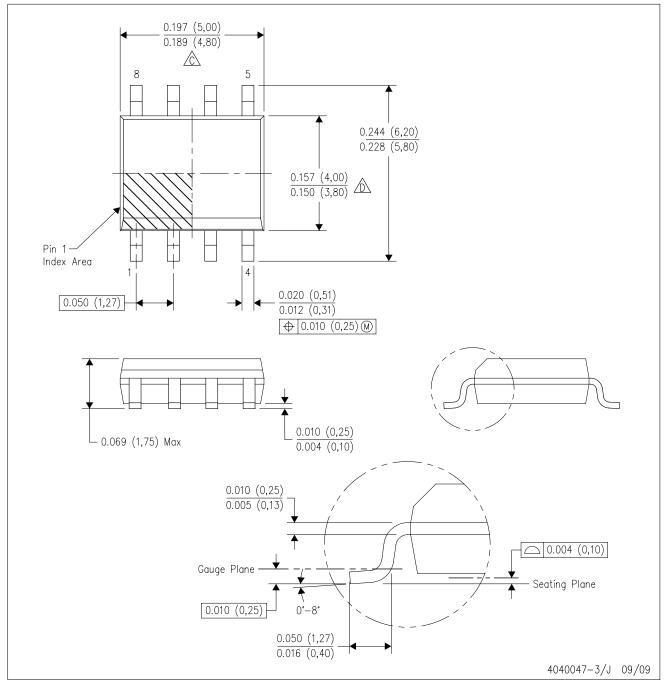
#### NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### D (R-PDSO-G8)

#### PLASTIC SMALL-OUTLINE PACKAGE



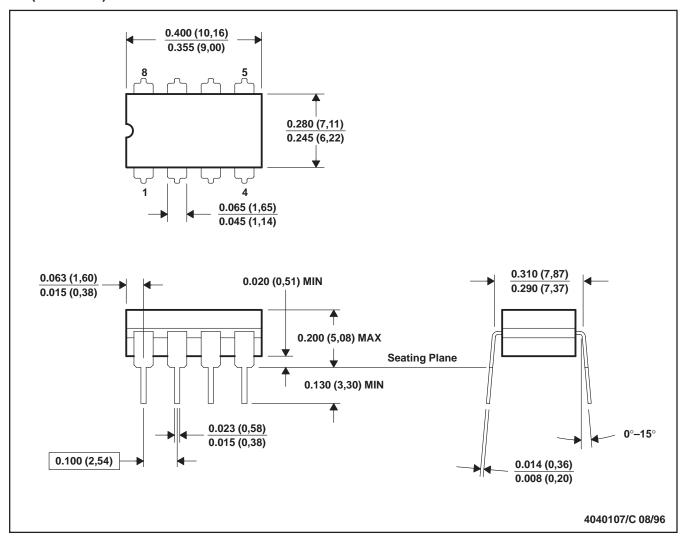
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



#### JG (R-GDIP-T8)

#### **CERAMIC DUAL-IN-LINE**



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

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